



NM27LV512

524,288-Bit (64k x 8) Low Voltage EPROM

General Description

The NM27LV512 is a high performance Low Voltage Electrical Programmable Read Only Memory. It is manufactured using National's latest 1.2 μ CMOS split gate SVG EPROM technology. This technology allows the part to operate at speeds as fast as 200 ns over commercial temperature (0°C to 70°C), and 250 ns over industrial temperatures (-40°C to +85°C).

This Low Voltage and Low Power EPROM is designed with power sensitive handheld and portable battery products in mind. This allows for code storage of firmware for applications like notebook computers, palm top computers, cellular phones, and HDD.

National still maintains its' commitment to high quality and reliability with EPI processing on the NM27LV512. Latch-up immunity is guaranteed for stresses up to 200 mA on address and data pins from -1V to V_{CC} + 0.3V. ESD protection is guaranteed 2000V.

Small outline packages are just as critical to portable applications as Low Voltage and Low Power. National Semiconductor has foreseen this need and provides win-

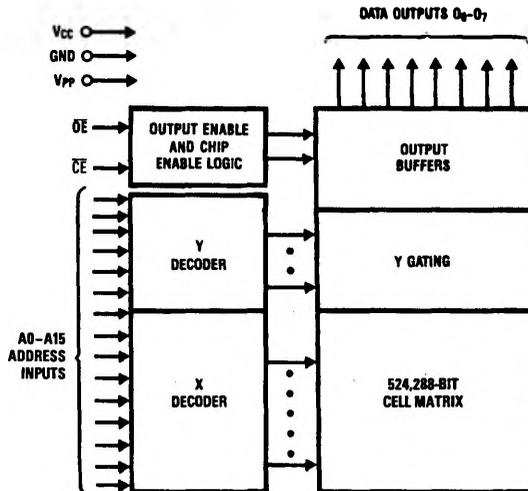
dowed LCC for prototyping and software development, PLCC for production runs, and TSOP for PC board sensitive users.

The NM27LV512 is one member of National's growing Low Voltage product family.

Features

- 3.0V to 5.5V operation
- 200 ns access time
- Low current operation
 - 12 mA I_{CC} Active Current @ 5 MHz
 - 20 μ A I_{CC} Standby Current @ 5 MHz
- Ultra Low Power operation
 - 50 μ W Standby Power @ 3.3V
 - 50 mW Active Power @ 3.3V
- High reliability EPI processing
 - Latch up immunity up to 200 mA
 - 2000V ESD protection
- Surface mount package options
 - 28-pin CERPACK
 - 28-pin PLCC
 - 28-pin TSOP

Block Diagram



TL/D/11375-1